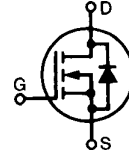


# Standard Power MOSFET

IXTH / IXTM 5N100  
IXTH / IXTM 5N100A

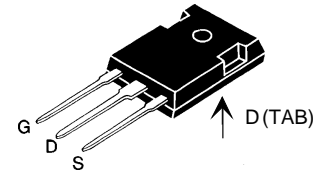
$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
1000 V	5 A	2.4 $\Omega$
1000 V	5 A	2.0 $\Omega$

## N-Channel Enhancement Mode

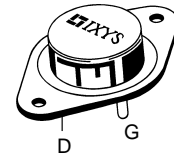


Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	1000	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	1000	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	5	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	20	A
$P_D$	$T_C = 25^\circ\text{C}$	180	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

### TO-247 AD (IXTH)



### TO-204 AA (IXTM)



G = Gate, D = Drain,  
S = Source, TAB = Drain

### Features

- International standard packages
- Low  $R_{DS(on)}$  HDMOST™ process
- Rugged polysilicon gate cell structure
- Low package inductance (< 5 nH)
  - easy to drive and to protect
- Fast switching times

### Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

### Advantages

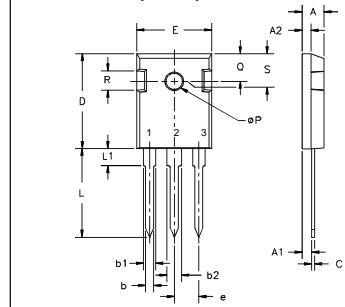
- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 3\text{ mA}$	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20 V_{DC}$ , $V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = 0.8 \cdot V_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$			250 $\mu\text{A}$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300\text{ }\mu\text{s}$ , duty cycle $d \leq 2\%$			2.4 $\Omega$ 2.0 $\Omega$

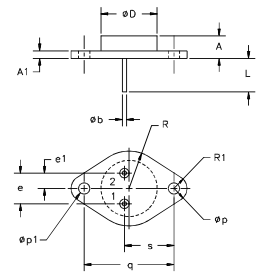
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	4	6	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2600	pF
$C_{oss}$			180	pF
$C_{rss}$			45	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 4.7\ \Omega$ , (External)		35	100 ns
$t_r$			20	50 ns
$t_{d(off)}$			100	200 ns
$t_f$			30	80 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		88	130 nC
$Q_{gs}$			21	30 nC
$Q_{gd}$			38	70 nC
$R_{thJC}$			0.7	K/W
$R_{thCK}$		0.25		K/W

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			5 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			20 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	900		ns

**TO-247 AD (IXTH) Outline**

 Terminals: 1 - Gate  
 2 - Drain  
 3 - Source  
 Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

**TO-204AA (IXTM) Outline**

 Pins 1 - Gate 2 - Source  
 Case - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	6.4	11.4	.250	.450
A <sub>1</sub>		3.42		.135
∅b	.97	1.09	.038	.043
∅D		22.22		.875
e	10.67	11.17	.420	.440
e <sub>1</sub>	5.21	5.71	.205	.225
L	7.93		.312	
∅p	3.84	4.19	.151	.165
∅p <sub>1</sub>	3.84	4.19	.151	.165
q	30.15	BSC	1.187	BSC
R		13.33		.525
R <sub>1</sub>		4.77		.188
s	16.64	17.14	.655	.675

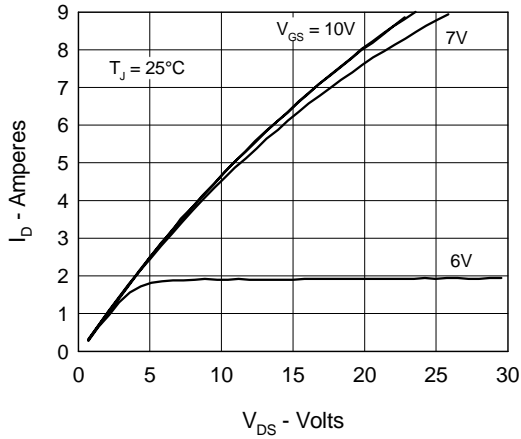
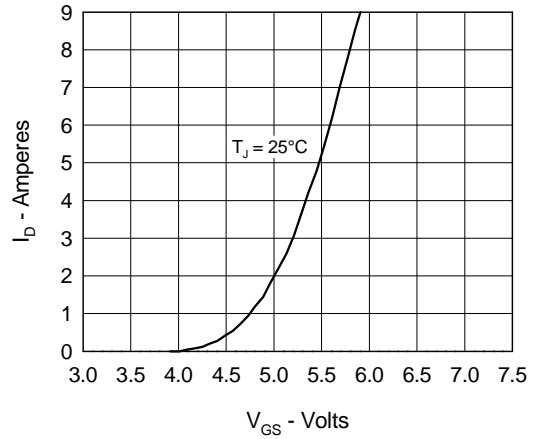
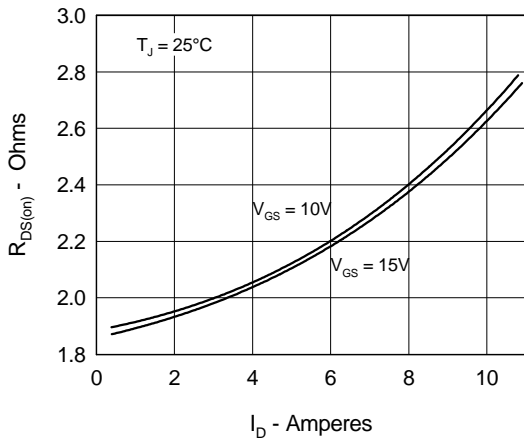
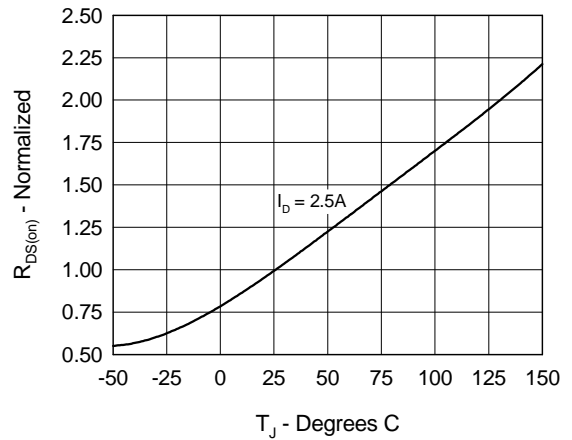
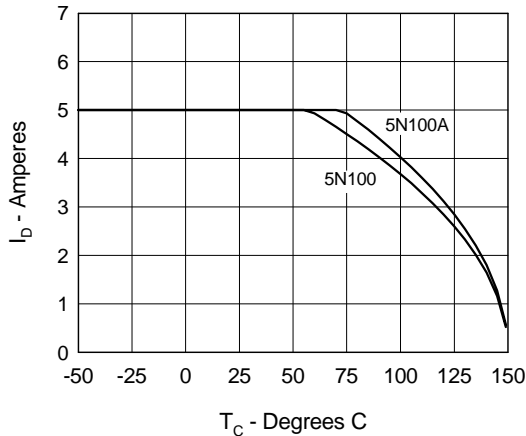
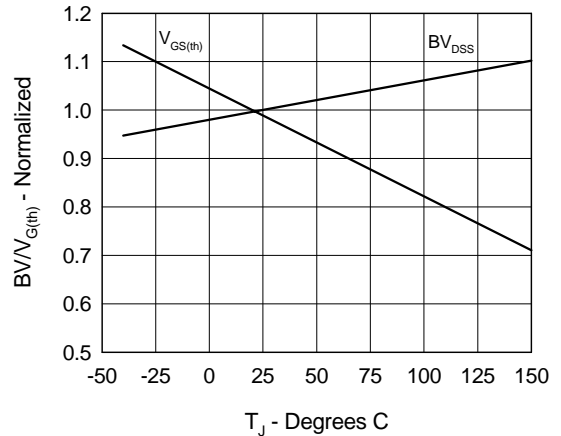
**Fig. 1 Output Characteristics**

**Fig. 2 Input Admittance**

**Fig. 3  $R_{DS(on)}$  vs. Drain Current**

**Fig. 4 Temperature Dependence of Drain to Source Resistance**

**Fig. 5 Drain Current vs. Case Temperature**

**Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage**


Fig.7 Gate Charge Characteristic Curve

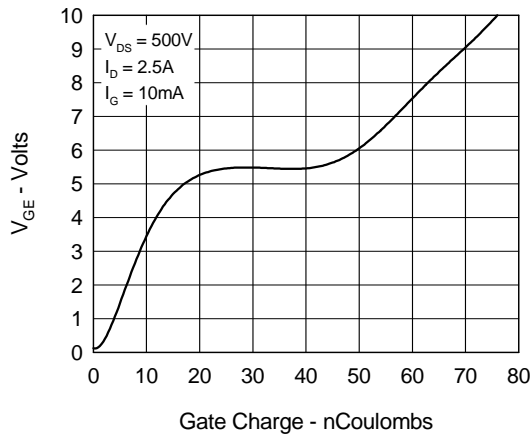


Fig.8 Forward Bias Safe Operating Area

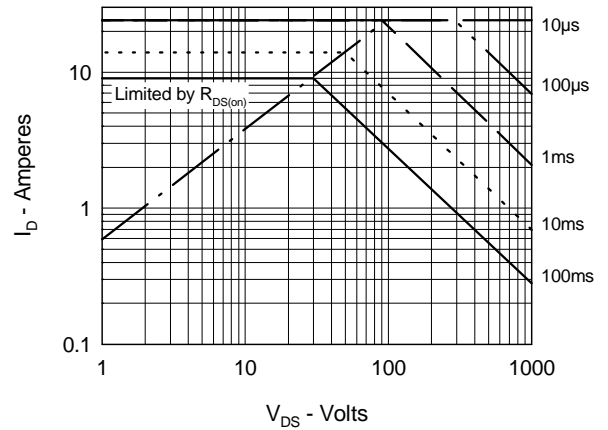


Fig.9 Capacitance Curves

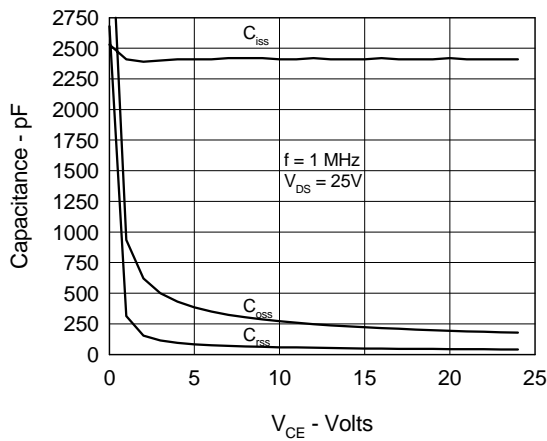


Fig.10 Source Current vs. Source to Drain Voltage

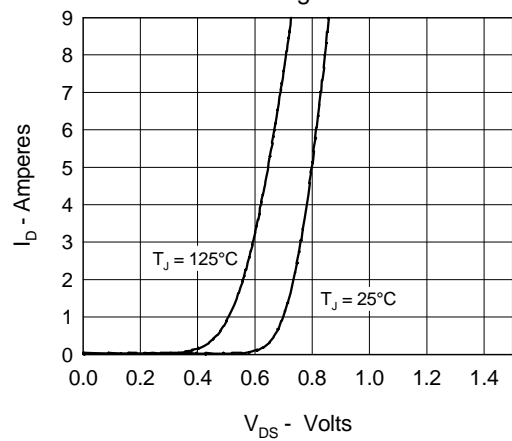


Fig.11 Transient Thermal Impedance

